Claims:

1. A method for depositing a material on a substrate, comprising:
providing a silicon substrate having:
a field region;
a backside, and
a feature extending from the field region toward the backside, the feature having at least one sidewall and a bottom surface;
depositing a conformal barrier layer over the field region, the at least one sidewall and the bottom surface;
removing a portion of the conformal barrier layer from the bottom surface of the feature to expose the silicon substrate;
depositing a metal seed layer on the exposed silicon substrate at the bottom of the feature; and
exposing the substrate to an electroplating process by flowing a current through the backside of the silicon substrate to form a metal layer on the metal seed layer, wherein exposing the substrate to an electroplating process by flowing a current through a backside of the substrate to form a metal layer on the metal seed layer comprises exposing the backside of the substrate to a potassium hydroxide solution and exposing the seed layer to a copper containing solution.